Substitute for F rm 1449/PTO Complete if Known **Application Number** Not yet assigned INFORMATION DISCLOSURE Filing Date Herewith STATEMENT BY APPLICANT First Named Inventor: Justin K. Brask et al. (use as many sheets as necessary) Art Unit Not yet assigned **Examiner Name** Not yet assigned 1 ٥f 2 Attorney Docket Number 042390P15744C Sh t **U.S. PATENT DOCUMENTS** Cite No. **Publication Date** Examiner Name of Patentee or Pages, Columns, Lines, Initials* **Document Number** MM-DD-YYYY Applicant of Cited Document Where Relevant Passages or Relevant Number-Kind Code²(# known) Figures Appear Chau et al. 5,8,625,217 4/29/1997 US-5,783,478 7/21/1998 Chau et al. US-5,891,798 4/6/1999 Doyle et al. US-6,306,742 B1 10/23/2001 Doyle et al. US-6.184.072 B1 2/6/2001 Kaushik et al. US-6,420,279 B1 7/16/2002 Ono et al. US-6,544,906 B2 4/8/2003 Rotondaro et al. US-6,617,209 B1 9/9/2003 Chau et al. us-2003/0032303 A1 2/13/2003 Yu et al. US-2003/0045080 A1 3/6/2003 Visokay et al. us. US-

FOREIGN PATENT DOCUMENTS											
Examiner Initials*	Cite No.¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ⁴ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Т					

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Examiner Signature	Christy Horacek	Date Considered	6/24/05

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(use as many sheets as necessary)					Art Unit	Unknown				
			 	·	Examiner Name	Unknown				
Sh et	2 of 2			2	Attorney Docket Number	042390P15744C				
NON PATENT LITERATURE DOCUMENTS										
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published								
ON		Doug Barlage et al. "High-Frequency Response of 100nm Integrated CMOS Transistors with High-K Gate Dielectrics", 2001 IEEE, 4 pgs.								
CV		Robert Chau et al., "A 50nm Depleted-Substrate CMOS Transitor (DST), 2001 IEEE, 4 pgs.								
CX		"A Method for Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/082,530, Filed February 22, 2002								
CY		"A Method for Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/285,915, Filed October 31, 2002								
CK		"A Method for Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/288,043, Filed November 5, 2002								
OY		"A Method for Making a Semiconductor Device Having an Ultra-Thin High-K Gate Dielectric", Serial No. 10/315,268, Filed December 10, 2002								
CX		"A Method for Making a Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/338,174, Filed January 7, 2003								
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